

# HCH65S10D1

## SiC Silicon Carbide Schottky Diode

650V, 10A

### Description

The 650V SiC is an advanced Power Master Semiconductor's silicon carbide diode family. This technology combines the benefits of excellent low forward voltage and robustness. Consequently, the SiC family is suitable for application requiring high power efficiency.

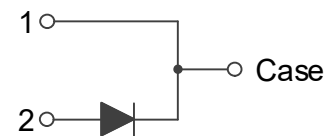
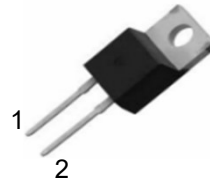
### Applications

- Power Factor Correction
- Industrial Power Supplies
- Solar Inverter, UPS

### Features

| $V_{RRM}$ | $I_F$ | $T_{J,max}$ | $Q_C$ |
|-----------|-------|-------------|-------|
| 650 V     | 10 A  | 175 °C      | 39 nC |

- No reverse recovery current
- Low forward voltage
- 175°C Max junction temperature
- High surge current capability
- Switching behavior independent of temperature
- Pb-Free, Halogen Free and RoHS compliant



### Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

| Symbol         | Parameter                                  |                                           | Value       | Unit                 |
|----------------|--------------------------------------------|-------------------------------------------|-------------|----------------------|
| $V_{RRM}$      | Repetitive Peak Reverse Voltage            |                                           | 650         | V                    |
| $I_F$          | Forward Current                            | $T_C=147^\circ\text{C}$                   | 10          | A                    |
| $I_{F,SM}$     | Non-Repetitive Forward Surge Current       | $T_C=25^\circ\text{C}, t_p=10\text{ ms}$  | 55          | A                    |
|                |                                            | $T_C=150^\circ\text{C}, t_p=10\text{ ms}$ | 46          | A                    |
| $I_{F,Max}$    | Non-Repetitive Peak Forward Current        | $T_C=25^\circ\text{C}, t_p=10\text{ us}$  | 665         | A                    |
|                |                                            | $T_C=150^\circ\text{C}, t_p=10\text{ us}$ | 565         | A                    |
| $I^2dt$ value  | $\int I^2 dt$                              | $T_C=25^\circ\text{C}, t_p=10\text{ ms}$  | 15.1        | $\text{A}^2\text{s}$ |
|                |                                            | $T_C=150^\circ\text{C}, t_p=10\text{ ms}$ | 10.6        | $\text{A}^2\text{s}$ |
| $P_{tot}$      | Power Dissipation                          | $T_C=25^\circ\text{C}$                    | 94          | W                    |
| $T_J, T_{STG}$ | Operating Junction and Storage Temperature |                                           | -55 to +175 | $^\circ\text{C}$     |

### Thermal Characteristics

| Symbol          | Parameter                                  | Value | Unit               |
|-----------------|--------------------------------------------|-------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. | 1.6   | $^\circ\text{C/W}$ |

## Package Marking and Ordering Information

| Part Number | Top Marking | Package   | Packing Method | Quantity |
|-------------|-------------|-----------|----------------|----------|
| HCH65S10D1  | HCH65S10D1  | TO-220-2L | Tube           | 50 units |

## Electrical Characteristics (T<sub>C</sub> = 25°C unless otherwise noted)

| Symbol         | Parameter                 | Test Conditions                              | Min | Typ  | Max | Unit |
|----------------|---------------------------|----------------------------------------------|-----|------|-----|------|
| V <sub>F</sub> | Forward Voltage           | I <sub>F</sub> =10 A, T <sub>C</sub> =25°C   |     | 1.30 | 1.6 | V    |
|                |                           | I <sub>F</sub> =10 A, T <sub>C</sub> =175°C  |     | 1.45 | -   |      |
| I <sub>R</sub> | Reverse Current           | V <sub>R</sub> =650 V, T <sub>C</sub> =25°C  |     | -    | 100 | μA   |
|                |                           | V <sub>R</sub> =650 V, T <sub>C</sub> =175°C |     | -    | 300 |      |
| Q <sub>C</sub> | Total Capacitive Charge   | V <sub>R</sub> =400 V, T <sub>C</sub> =25°C  |     | 39   |     | nC   |
| C              | Total Capacitance         | V <sub>R</sub> =1 V, f=100 kHz               |     | 623  |     | pF   |
|                |                           | V <sub>R</sub> =400 V, f=100 kHz             |     | 60   |     |      |
| E <sub>C</sub> | Capacitance Stored Energy | V <sub>R</sub> =400 V, T <sub>C</sub> =25°C  |     | 5.7  |     | μJ   |

Typical Performance Characteristics

Figure 1. Power Derating

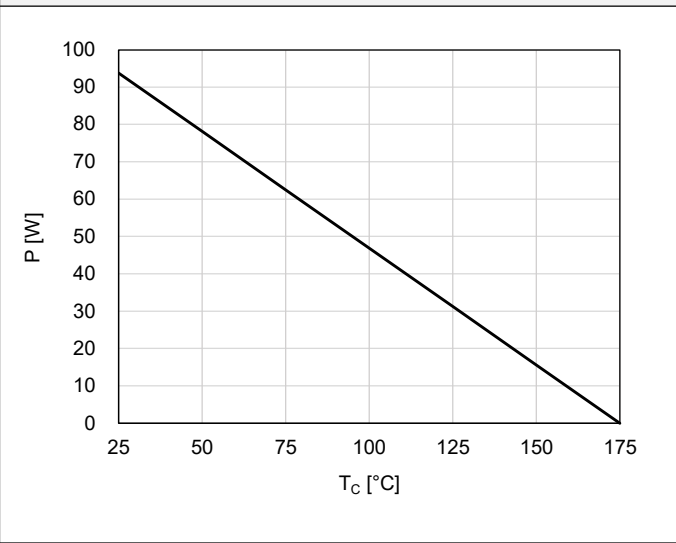


Figure 2. Current Derating

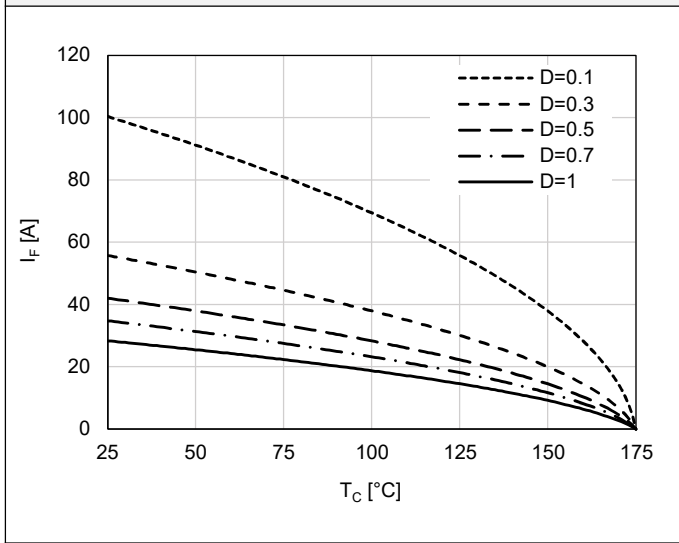


Figure 3. Forward Characteristics

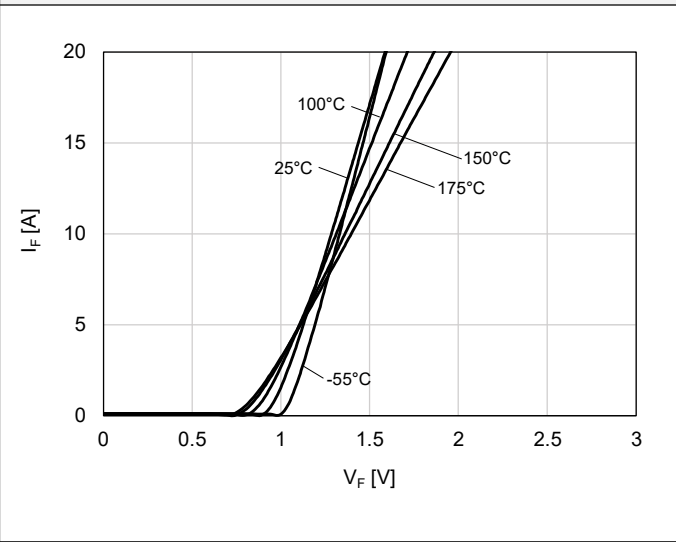


Figure 4. Reverse Characteristics

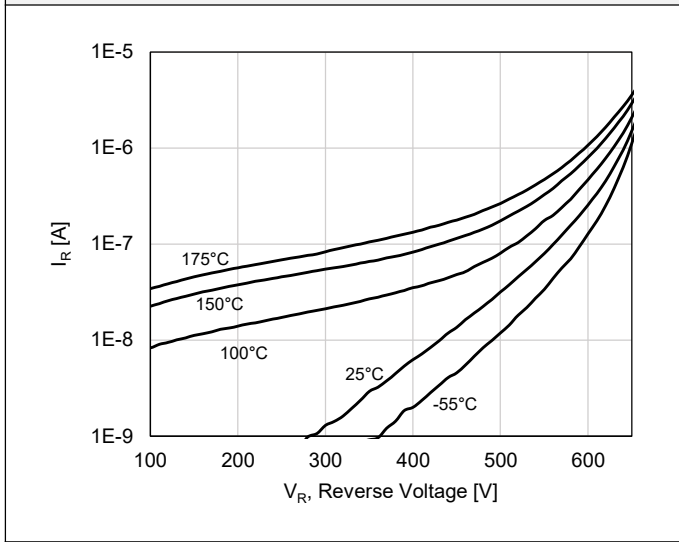


Figure 5. Capacitive Charge Characteristic

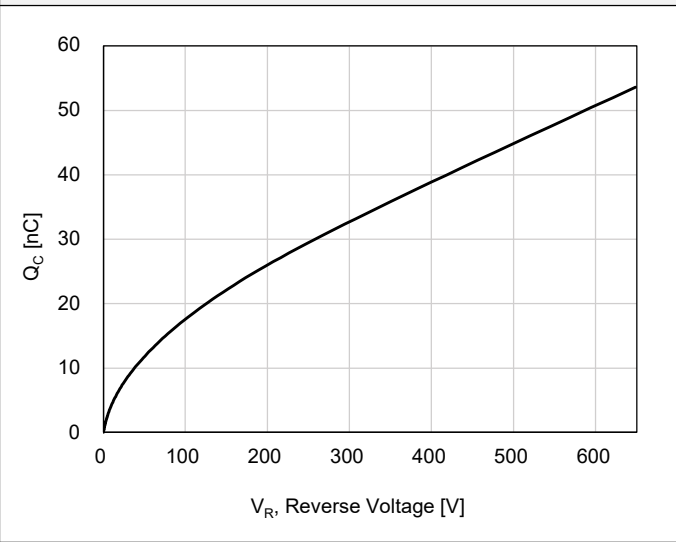
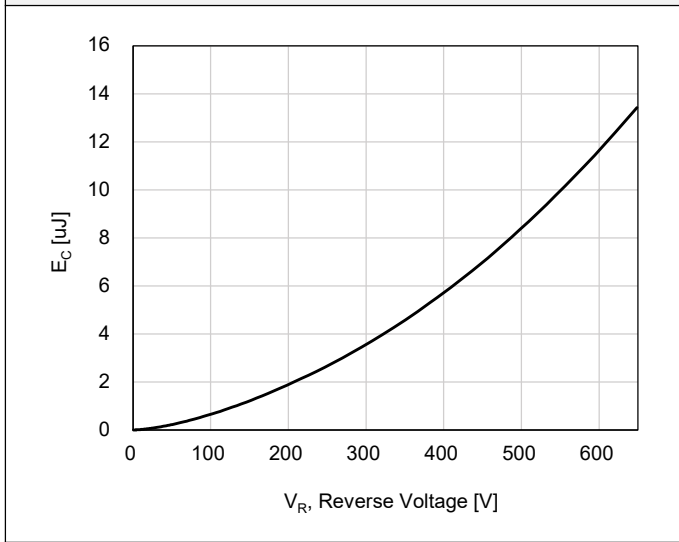


Figure 6. Capacitance Stored Energy



Typical Performance Characteristics

Figure 7. Capacitance Characteristic

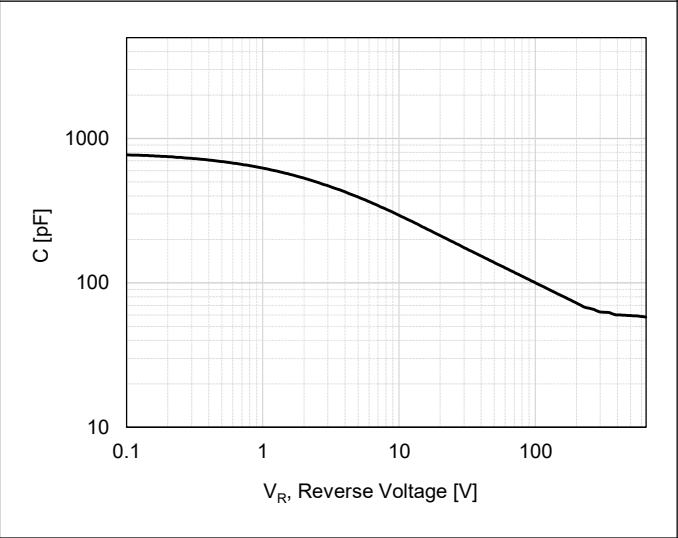
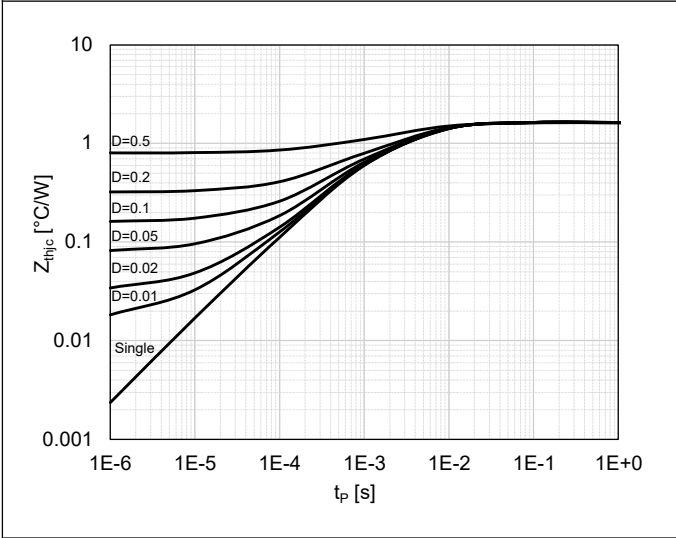


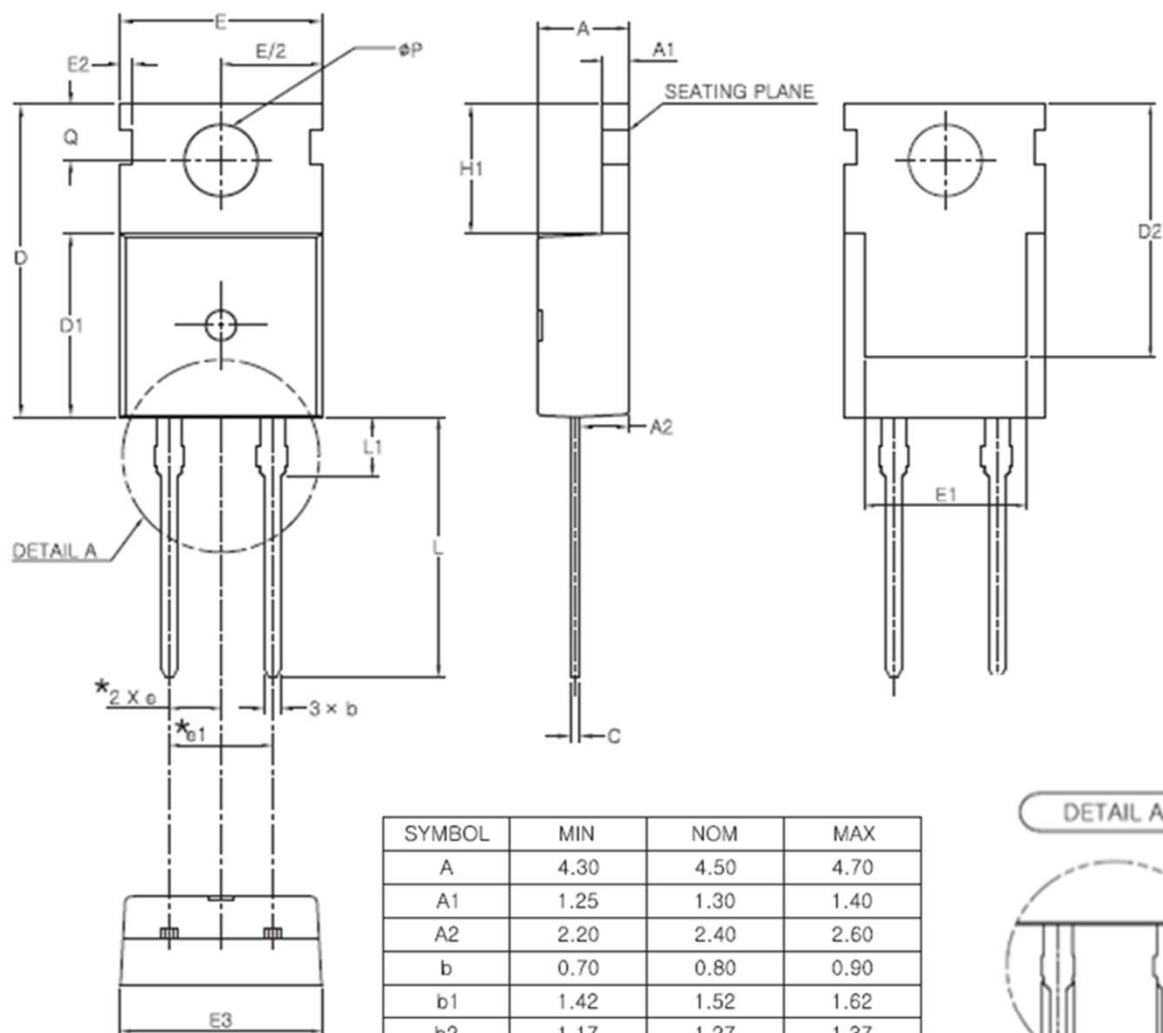
Figure 8. Transient Thermal Response Curve



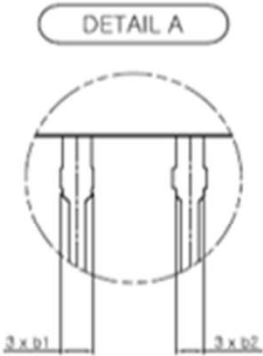
Package Outlines

TO-220-2L

TO-220-2L



| SYMBOL   | MIN      | NOM   | MAX   |
|----------|----------|-------|-------|
| A        | 4.30     | 4.50  | 4.70  |
| A1       | 1.25     | 1.30  | 1.40  |
| A2       | 2.20     | 2.40  | 2.60  |
| b        | 0.70     | 0.80  | 0.90  |
| b1       | 1.42     | 1.52  | 1.62  |
| b2       | 1.17     | 1.27  | 1.37  |
| c        | 0.45     | 0.50  | 0.60  |
| D        | 15.50    | 15.70 | 15.90 |
| D1       | 9.00     | 9.20  | 9.40  |
| D2       | (12.70)  |       |       |
| E        | 9.70     | 9.90  | 10.10 |
| E1       | (8.00)   |       |       |
| E2       | (0.60)   |       |       |
| E3       | 9.70     | 9.90  | 10.10 |
| e        | 2.54 BSC |       |       |
| e1       | 5.08 BSC |       |       |
| H1       | 6.30     | 6.50  | 6.70  |
| L        | 12.88    | 13.08 | 13.28 |
| L1       | (3.00)   |       |       |
| $\phi P$ | 3.50     | 3.60  | 3.70  |
| Q        | 2.70     | 2.80  | 2.90  |



\* Dimensions in millimeters